

**Silicon PNP Power Transistors**

**2N6489 2N6490 2N6491**

**DESCRIPTION**

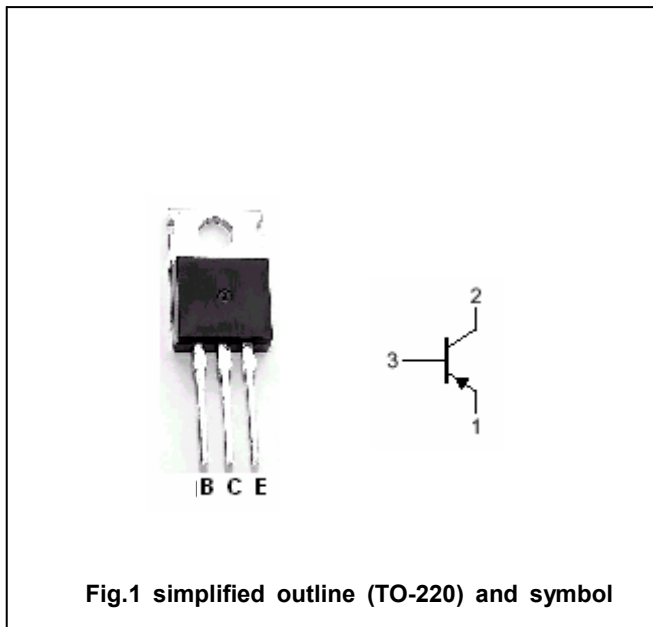
- With TO-220 package
- Excellent safe operating area
- Complement to type 2N6486 2N6487 2N6488 respectively

**APPLICATIONS**

- Power amplifier and medium speed switching applications

**PINNING**

| PIN | DESCRIPTION                          |
|-----|--------------------------------------|
| 1   | Emitter                              |
| 2   | Collector;connected to mounting base |
| 3   | Base                                 |



**Absolute maximum ratings(Ta=25°C)**

| SYMBOL           | PARAMETER                 | CONDITIONS           | VALUE   | UNIT |
|------------------|---------------------------|----------------------|---------|------|
| V <sub>CBO</sub> | Collector-base voltage    | 2N6489               | -50     | V    |
|                  |                           | 2N6490               | -70     |      |
|                  |                           | 2N6491               | -90     |      |
| V <sub>CEO</sub> | Collector-emitter voltage | 2N6489               | -40     | V    |
|                  |                           | 2N6490               | -60     |      |
|                  |                           | 2N6491               | -80     |      |
| V <sub>EBO</sub> | Emitter-base voltage      | Open collector       | -5      | V    |
| I <sub>C</sub>   | Collector current         |                      | -15     | A    |
| I <sub>B</sub>   | Base current              |                      | -5      | A    |
| P <sub>T</sub>   | Total power dissipation   | T <sub>C</sub> =25°C | 75      | W    |
| T <sub>j</sub>   | Junction temperature      |                      | 150     | °C   |
| T <sub>stg</sub> | Storage temperature       |                      | -65~150 | °C   |

**THERMAL CHARACTERISTICS**

| SYMBOL              | PARAMETER                                | MAX  | UNIT |
|---------------------|--|------|------|
| R <sub>th j-c</sub> | Thermal resistance from junction to case | 1.67 | °C/W |

## Silicon PNP Power Transistors

## 2N6489 2N6490 2N6491

## CHARACTERISTICS

T<sub>j</sub>=25 °C unless otherwise specified

| SYMBOL                | PARAMETER   | CONDITIONS                                  | MIN   | TYP.  | MAX  | UNIT         |    |              |
|-----------------------|---|---|---|---|------|--------------|----|--------------|
| V <sub>CEO(SUS)</sub> | Collector-emitter sustaining voltage                | 2N6489                                      | I <sub>C</sub> =-0.2A ; I <sub>B</sub> =0                               | -40   |      | V            |    |              |
|                       |   | 2N6490                                      |   | -60   |      |              |    |              |
|                       |   | 2N6491                                      |   | -80   |      |              |    |              |
| V <sub>CEsat-1</sub>  | Collector-emitter saturation voltage                | I <sub>C</sub> =-5A; I <sub>B</sub> =-0.5A  |   |   | -1.3 | V            |    |              |
| V <sub>CEsat-2</sub>  | Collector-emitter saturation voltage                | I <sub>C</sub> =-15A; I <sub>B</sub> =-5A   |   |   | -3.5 | V            |    |              |
| V <sub>BE-1</sub>     | Base-emitter on voltage                             | I <sub>C</sub> =-5A ; V <sub>CE</sub> =-4V  |   |   | -1.3 | V            |    |              |
| V <sub>BE-2</sub>     | Base-emitter on voltage                             | I <sub>C</sub> =-15A ; V <sub>CE</sub> =-4V |   |   | -3.5 | V            |    |              |
| I <sub>CEX</sub>      | Collector cut-off current<br>V <sub>BE</sub> =-1.5V | 2N6489                                      | V <sub>CE</sub> =-45V;<br>V <sub>CE</sub> =-40V; T <sub>C</sub> =150 °C |   |      | -0.5<br>-5.0 | mA |              |
|                       |   | 2N6490                                      |   | V <sub>CE</sub> =-65V;<br>V <sub>CE</sub> =-60V; T <sub>C</sub> =150 °C |      |              |    | -0.5<br>-5.0 |
|                       |   | 2N6491                                      |   | V <sub>CE</sub> =-85V;<br>V <sub>CE</sub> =-80V; T <sub>C</sub> =150 °C |      |              |    | -0.5<br>-5.0 |
| I <sub>CEO</sub>      | Collector cut-off current                           | 2N6489                                      | V <sub>CE</sub> =-20V; I <sub>B</sub> =0                                |   |      | -1.0         | mA |              |
|                       |   | 2N6490                                      |   | V <sub>CE</sub> =-30V; I <sub>B</sub> =0                                |      |              |    |              |
|                       |   | 2N6491                                      |   | V <sub>CE</sub> =-40V; I <sub>B</sub> =0                                |      |              |    |              |
| I <sub>EBO</sub>      | Emitter cut-off current                             | V <sub>EB</sub> =-5V; I <sub>C</sub> =0     |   |   | -1.0 | mA           |    |              |
| h <sub>FE-1</sub>     | DC current gain                                     | I <sub>C</sub> =-5A ; V <sub>CE</sub> =-4V  | 20  |   | 150  |              |    |              |
| h <sub>FE-2</sub>     | DC current gain                                     | I <sub>C</sub> =-15A ; V <sub>CE</sub> =-4V | 5   |   |      |              |    |              |

Silicon PNP Power Transistors

2N6489 2N6490 2N6491

PACKAGE OUTLINE

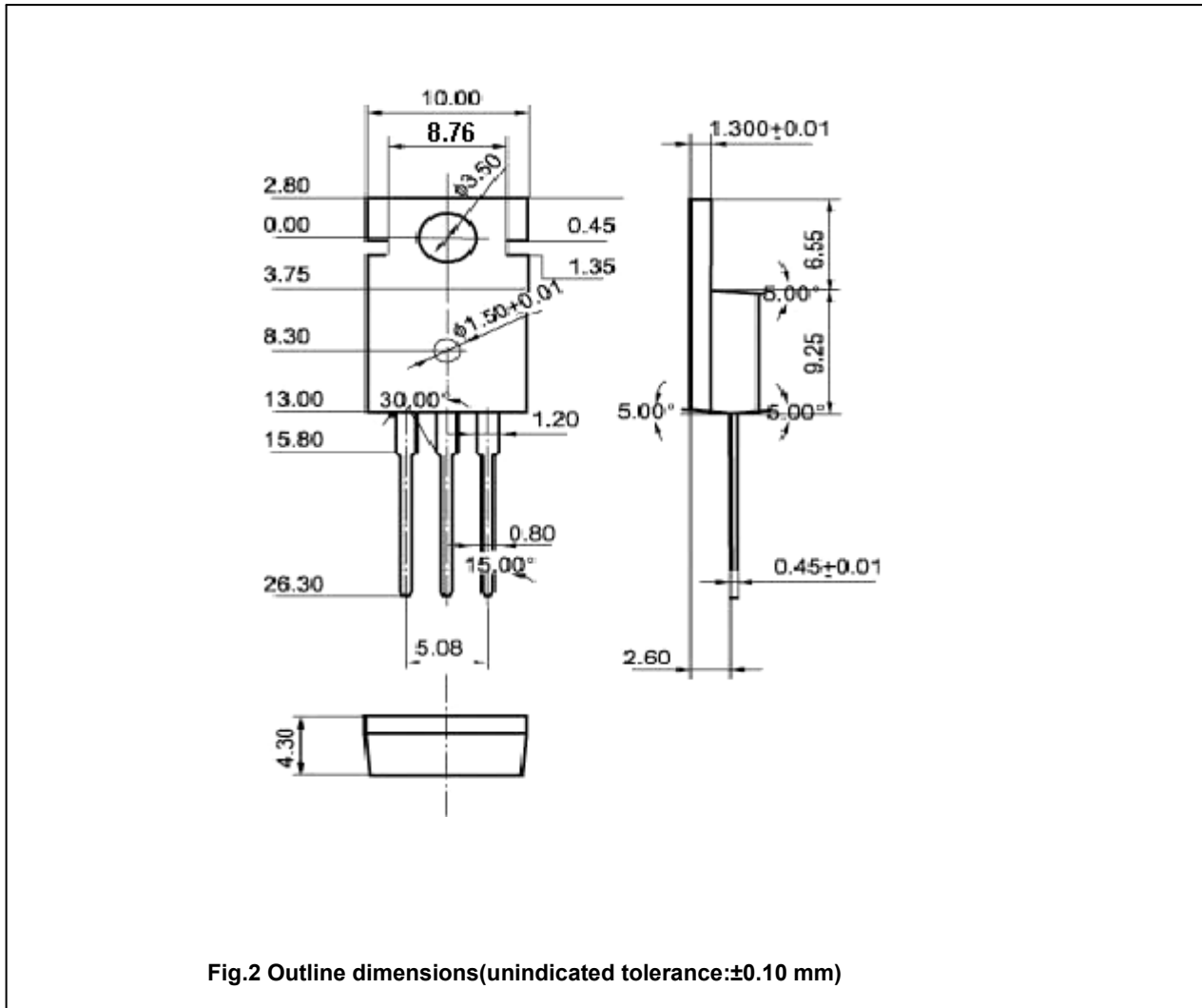


Fig.2 Outline dimensions(unindicated tolerance:±0.10 mm)